

**DESCRIPTIVE ABSTRACT**

This is a phase-change memory cell  
5 including between two electrical contacts (1, 2), a portion (3) in a memory material with amorphous-crystalline phase-change and vice versa, as a stack with a central area (3.1) located between two outmost areas (3.2, 3.3). An interface (3.21, 3.31), inert or  
10 quasi-inert from a physico-chemical point of view, is present between the so-called active central area (3.1) and each so-called passive outmost area (3.2, 3.3). Each passive outmost area (3.2, 3.3) is made in a material having a melting temperature higher than that  
15 of the material of the active central area (3.1).

Notably applied to PC RAM memories.

Fig. 1A.